

FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16790JB

Generic Copy

Issue Date: 23-Dec-2014

<u>TITLE</u>: Final PCN for wafer fabrication site addition of ON Semiconductor Niigata Co., Ltd. in Niigata, Japan.

PROPOSED FIRST SHIP DATE: starting on 16-Apr-2015

AFFECTED CHANGE CATEGORY(S): Wafer Fabrication Site Addition

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Yasuhiro.lgarashi@onsemi.com.

<u>SAMPLES</u>: Contact your local ON Semiconductor Sales Office or <u>Shigehito.Matsumoto@onsemi.com</u>

ADDITIONAL RELIABILITY DATA:

Contact your local ON Semiconductor Sales Office or Kazutoshi.Kitazume@onsemi.com

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact quality@onsemi.com

DESCRIPTION AND PURPOSE:

This is a Final Process Change Notification to announce about expanding from conventional Manufacturers UMC to newly wafer fabrication site. Additional fabrication site is ON Semiconductor Niigata Co., Ltd. (OSNC). OSNC is located in Niigata, Japan, obtained ISO9001 certification.

The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.

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RELIABILITY DATA SUMMARY

Group JB

Test:	Conditions:	Interval:	Results
Steady State Operating Life	Tj=150degC	1000 hrs	Pass
High Temperature Reverse Bias	Ta=150degC, VDSS = max	1000 hrs	Pass
Temp Humidity Storage	Ta=85degC, RH=85%	1000 hrs	Pass
Temperature Cycle	Ta=-55degC to 150degC 30min each	100 cycles	Pass
Pressure Cooker	Ta=121degC,2.03×10⁵Pa,100%	50 hrs	Pass
High Temperature Storage	Ta=150degC	1000 hrs	Pass
Resistance to Soldering heat (Refle	ow) Solder Temp.:260degC±5degC	10s	Pass
Solderability	Solder Temp.: 245degC±5degC	5 s	Pass

ELECTRICAL CHARACTERISTIC SUMMARY

There is no change in the electrical performance. Datasheet specifications remain unchanged.

CHANGED PART IDENTIFICATION

No change to current part marking will occur. Marking traceability codes will be able to identify wafer fab die source.

List of Affected General Parts:

Group JB

ATP112-TL-H ATP202-TL-H

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